

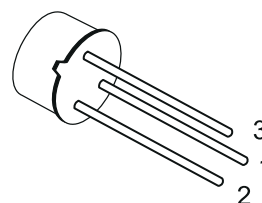
SILICON PNP TRANSISTORS

- SGS-THOMSON PREFERRED SALESTYPES
- PNP TRANSISTOR

DESCRIPTION

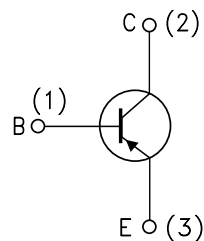
The 2N5415, 2N5416 are high voltage silicon epitaxial planar PNP transistors in Jedec TO-39 metal case designed for use in consumer and industrial line-operated applications.

These devices are particularly suited as drivers in high-voltage low current inverters, switching and series regulators.



TO-39

INTERNAL SCHEMATIC DIAGRAM



SC08810

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		2N5415	2N5416	
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	-200	-350	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	-200	-300	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	-4	-6	V
I_C	Collector Current	-1		A
I_B	Base Current	-0.5		A
P_{tot}	Total Dissipation at $T_c \leq 25^\circ\text{C}$	10		W
P_{tot}	Total Dissipation at $T_{amb} \leq 50^\circ\text{C}$	1		W
T_{stg}	Storage Temperature	-65 to 200		$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	200		$^\circ\text{C}$

2N5415 / 2N5416

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	17.5	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	175	$^{\circ}C/W$

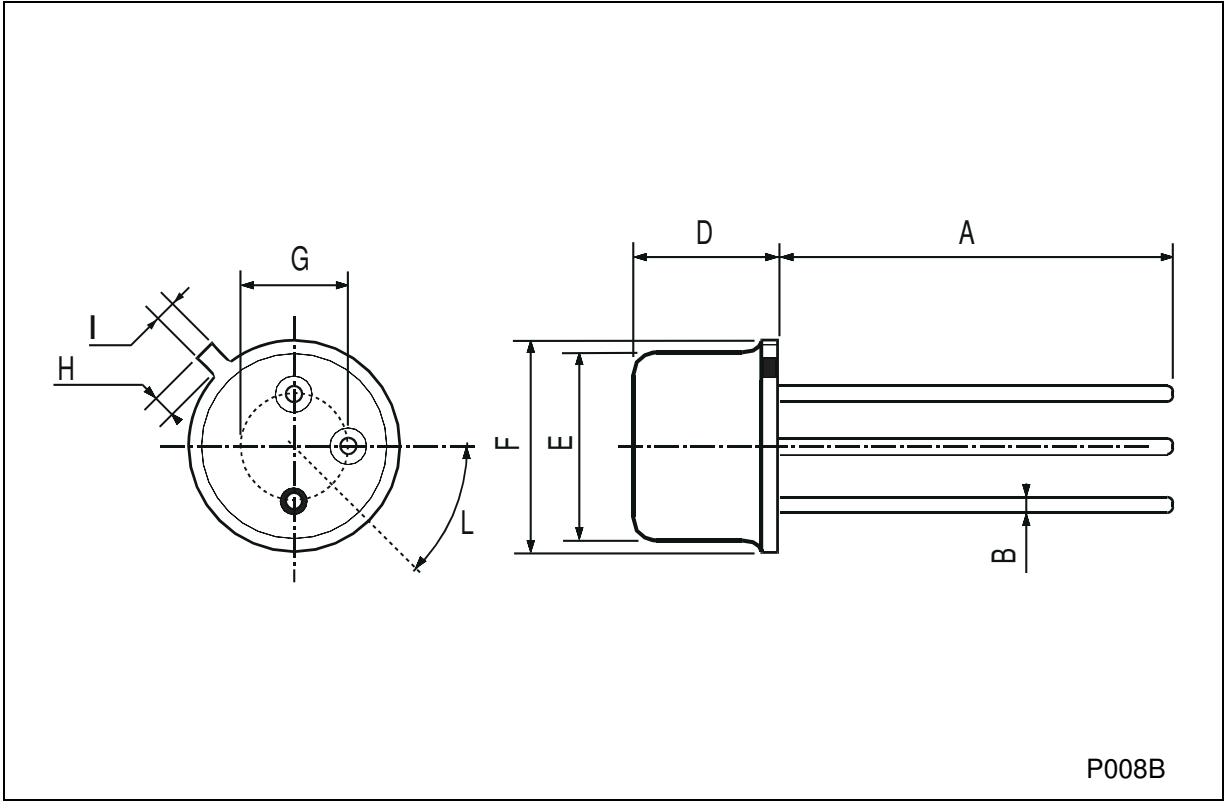
ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current ($I_E = 0$)	for 2N5415 $V_{CB} = -175 V$ for 2N5416 $V_{CB} = -280 V$			-50 -50	μA μA
I_{CEO}	Collector Cut-off Current ($I_B = 0$)	$V_{CE} = -150 V$			-50	μA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	for 2N5415 $V_{EB} = -4 V$ for 2N5416 $V_{EB} = -6 V$			-20 -20	μA μA
V_{CER}^*	Collector-Emitter Sustaining Voltage	$I_C = -50 mA$ $R_{BE} = 50\Omega$ for 2N5416	-350			V
$V_{CEO(sus)}^*$	Collector-Emitter Sustaining Voltage	$I_C = -10 mA$ for 2N5415 for 2N5416	-200 -300			V V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = -50 mA$ $I_B = -5 mA$			-2.5	V
V_{BE}^*	Base-Emitter Voltage	$I_C = -50 mA$ $V_{CE} = -10 V$			-1.5	V
h_{FE}^*	DC Current Gain	$I_C = -50 mA$ $V_{CE} = -10 V$ for 2N5415 for 2N5416	30 30		150 120	
h_{fe}	Small Signal Current Gain	$I_C = -5 mA$ $V_{CE} = -10 V$ $f = 1KHz$	25			
f_T	Transition frequency	$I_C = -10 mA$ $V_{CE} = -10 V$ $f = 5MHz$	15			MHz
C_{CBO}	Collector Base Capacitance	$I_E = 0$ $V_{CB} = -10 V$ $f = 1MHz$			25	pF

* Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

TO-39 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	12.7			0.500		
B			0.49			0.019
D			6.6			0.260
E			8.5			0.334
F			9.4			0.370
G	5.08			0.200		
H			1.2			0.047
I			0.9			0.035
L	45° (typ.)					



Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1997 SGS-THOMSON Microelectronics - Printed in Italy - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES
Australia - Brazil - Canada - China - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -
Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A
...